

ACTIVE PIXEL SENSOR ARRAY RESET

5 **Field of the Invention**

The invention relates generally to image sensing circuits, and more particularly to the resetting of active pixel sensor arrays.

Background of the Invention

10 CMOS image sensor arrays can employ several types of pixels. Passive pixel sensor cells are comprised of a simple photodiode and an access transistor. Active pixel sensor (APS) cells have added features including a reset transistor and a source follower amplifier.

15 A conventional APS sensing array is composed of individual light sensitive transducers called pixels that are organized in rows and columns. One typical pixel arrangement is composed of a photodiode (with junction capacitance), a reset transistor with a reset gate, an amplifier transistor, and a row select transistor.

20 During the reset cycle, charge is transferred onto the capacitive element through the reset transistor. An integration cycle allows charge from the capacitive element to be discharged through the photodiode. The remaining charge is then sampled by the amplifying gate and transferred to column amplifiers through the row select transistor. Upon completion of this cycle, the capacitive element in the array must be reset via the
25 reset transistor. At this moment, a substantial amount of charge can be driven onto the substrate, raising the substrate bias voltage. Since the substrate is common for both the sensor array and peripheral circuitry, a significant increase in substrate charge increases the substrate bias voltage, which in turn can cause a circuit malfunction referred to as latch-up.

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Latch-up is defined as the generation of a low-impedance path in CMOS devices between the power supply rail and the ground rail. It is a well known fact that, under certain conditions, a parasitic PNP junction can be created in a CMOS integrated circuit, resulting in the latch-up and possibly destruction of the CMOS integrated circuit.

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Latch-up is a parasitic conduction mechanism to which CMOS structures have an inherent vulnerability. It is a thyristor operating mechanism that can be triggered in PNP structures. If any such PNP structure is triggered into latch-up on a chip, large currents can flow and the results are usually irreversibly catastrophic for the entire chip.

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Traditionally, integrated circuit designers have often relied on the fact that, typically, the operating characteristics of a CMOS integrated circuit are insufficient to surpass the high current threshold for triggering a latch-up. The potential problem is evaded by placing many substrate connections around the circuit. The substrate connections can draw off any potential current overload and prevent the latch-up triggering. However, in imaging circuitry, the fill factor, or percentage of the total pixel real estate that is effectively photosensitive, is significantly reduced if substrate connections were to be integrated within the cell. It is therefore impractical to place substrate connections within the array. In conventional APS imaging arrays the array size and the amount of charge being discharged upon reset is insufficient to cause latch-up, but due to the increasing size of sensor arrays, (1.3Mpixels), the charge increase must be considered.

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Several methods are used to prevent circuit latch-up, including well definition and the reduction of the lateral resistance of the n-tub. Well definition can effectively prevent PNP junction formation particularly for small circuits; however, the amount of charge related to an array reset can be too great for sufficient latch-up prevention using the well definition method. Since the presence of large lateral resistance in the n-tubs has been found to cause latch-up, it was felt that the reduction of lateral resistance may prevent latch-up. Although this method is proven to be effective, it cannot handle large currents.

Additionally, a change in the process for semiconductor substrates also increases costs, which should be minimized for production.

United States Patent No. 5,881,184 which was issued on March 9, 1999, describes a pixel for an imager in which the reset transistor either has two functions or is replaced by two reset transistors. In the latter case, the only way that the pixel can be reset is if a reset signal is applied to the gates of both of the transistors. The advantage of this is that each pixel can be reset individually rather than having all of the pixels in a row reset at the same time. This reference does not address the problem of the occurrence of latch-up during pixel resetting.

Therefore, there is a need for a method and apparatus for safely resetting active pixel sensor arrays without a significant increase in current that may cause destructive latch-up.

Summary of the Invention

The invention is directed to a method and apparatus resetting an array of active pixel sensors (APS) arranged in rows and columns on a substrate.

In accordance with one aspect of this invention, the resetting process comprises the sequential pre-resetting of groups of one or more sensors in the array and then simultaneously resetting all of the sensors. The groups may be formed from one or more adjacent or non-adjacent individual sensors, rows or columns of sensors. The process may further include the step of detecting the bias voltage present on the array substrate to determine the number of sensors in the groups being pre-reset.

In accordance with another aspect of this invention, the apparatus for resetting the array of active pixel sensors which are arranged in rows and columns comprises a controller which is coupled to the sensor array for applying signals to the array for sequentially pre-resetting groups of one or more sensors in the array and then for simultaneously applying a signal to all of the sensors in the sensor array for resetting the

entire array. The apparatus may further include a detector for sensing the bias voltage of the sensor array substrate for the controller to determine the number of sensors in each group being pre-reset. The groups of sensors being pre-reset may include one or more adjacent or non-adjacent individual sensors or rows or columns of sensors.

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Other aspects and advantages of the invention, as well as the structure and operation of its various embodiments, will become apparent to those ordinarily skilled in the art upon review of the following description in conjunction with the accompanying drawings.

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Brief Description of the Drawings

The invention will be described with reference to the accompanying drawings, wherein:

Figure 1 is a block diagram of a typical image sensor array;

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Figure 2 is a circuit diagram of an active pixel sensor (APS) cell;

Figure 3 illustrates a block diagram of the sensor array in accordance with the present invention; and

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Figure 4 illustrates a block diagram of the sensor array of a further embodiment of the present invention including bias voltage sensing means.

Detailed Description of the Invention

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Referring to figure 1, there is shown a block diagram of a typical image sensor array 10. The sensor array 10 consists of active pixel sensor (APS) cells 11 arranged in rows 1 to n and columns 1 to m. The columns 1 to m of APS cells 11 are provided a voltage Vdd from a voltage supply 12 through lines VR₁ to VR_m. In addition, each row 1 to n of APS cells 11 simultaneously receive reset enable signals RRE₁ to RRE_n from a reset signal 13 on lines 14₁ to 14_n to reset the sensor circuits 11. Access to each horizontal row 1 to n of APS cells 11 is provided by applying individual access signals

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RA_1 to RA_n which are normally pulses of equal amplitude but spaced in time via row lines 15_1 to 15_n from a row address decoder 16. The columns 1 to m of APS cells 11 are connected via data lines DL_1 to DL_m which are coupled to column sense amplifiers 17 to amplify the image signal. Thus the rows 1 to n of cells 11 are simultaneously reset by signals RRE_1 to RRE_n for sensing the incident light on the cells 11 whereas the sequential detecting of the level of incident light in the rows 1 to n of cells 11 is initiated by access signals RA_1 to RA_n and received on data lines DL_1 to DL_m .

A typical three transistor APS cell 11 is illustrated in figure 2. The cell 11 consists of a photodiode 21 which is inherently in parallel with a diffusion 26 acting as a capacitor coupled to the source of a reset transistor 22 and the gate of a transistor 23 which acts as a source follower amplifier. The drains of the reset transistor 22 and of the amplifying transistor 23 are normally connected to a supply voltage Vdd through a voltage line VR_m , however the reset transistor 22 and the amplifying transistor 23 may be connected to different voltage sources. The amplifying transistor 23 source is coupled to a data line DL_m through an access transistor 24. When activated, the reset transistor 22 places charge on the diffusion 26 from the supply voltage Vdd. This charge is drained through the photodiode 21 at a rate proportional to the intensity of incident light on the photodiode 21. A signal proportional to this intensity can be read from the cell 11 on the dataline DL_m by enabling the access transistor 24.

During normal operation, the voltage Vdd supplied to the drain of the reset transistor 22 is common to every cell 11 (i.e. pixel) in the array 10. Each row 1 to n of cells 11 simultaneously receives a reset enable signal RRE_1 to RRE_n respectively via a row reset line 14_1 to 14_n . The reset enable signals RRE_1 to RRE_n are active when at a logical high and all have the same amplitude which may be substantially at the level of the supply voltage Vdd. Again, during normal operation, the voltage level 13 associated with this logical high is common throughout the array. This means that all diffusions 26 acting as capacitors are reset to the same level, ie the same amount of reset charge is placed on the node of the photodiode 21 for every cell 11.

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The present invention can also be applied to variations of the active pixel sensor array, such as variations in the structure of the active pixel sensor. For example, a 4T or 5T structure can be employed, where a global reset is necessary in order to acquire a proper image.

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While the invention has been described according to what is presently considered to be the most practical and preferred embodiments, it must be understood that the invention is not limited to the disclosed embodiments. Those ordinarily skilled in the art will understand that various modifications and equivalent structures and functions may be made without departing from the spirit and scope of the invention as defined in the claims. Therefore, the invention as defined in the claims must be accorded the broadest possible interpretation so as to encompass all such modifications and equivalent structures and functions.

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